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LINEAR SYSTEMS

Linear Integrated Systems

df.dzsc.com

FEATURES						
DIRECT REPLACEMENT FOR INTERSIL 3N190 & 3N191						
LOW GATE LEAKAGE CURRENT	I _{GSS} ≤ ±10pA					
LOW TRANSFER CAPACITANCE	C _{rss} ≤ 1.0pF					
ABSOLUTE MAXIMUM RATINGS ¹						
@ 25 °C (unless otherwise stated)						
Maximum Temperatures						
Storage Temperature	-65 to +150 °C					
Operating Junction Temperature	-55 to +135 °C					
Maximum Power Dissipation						
Continuous Power Dissipation One Side	300mW					
Continuous Power Dissipation Both Sides	525mW					
Maximum Current	itops.					
Drain to Source ²	50mA					
Maximum Voltages						
Drain to Gate ²	30V					
Drain to Source ²	30V					
Transient Gate to Source ^{2,3}	±125V					
Gate to Gate	±80V					

捷多邦,专业PCB打样工厂,24小时加急出货

<u>3N190 3N191</u>

P-CHANNEL DUAL MOSFET ENHANCEMENT MODE





MATCHING CHARACTERISTICS @ 25 °C (unless otherwise stated) (V_{BS} = 0V unless otherwise stated)

SYMBOL	CHARACTERISTIC	MIN	TYP	MAX	UNITS	CONDITIONS
$g_{\rm fs1}/g_{\rm fs2}$	Forward Transconductance Ratio	0.85		1.0		V _{DS} = -15V, I _D = -500μA, <i>f</i> = 1kHz
V _{GS1-2}	Gate to Source Threshold Voltage			100	mV	V _{DS} = -15V, I _D = -500µA
$\frac{\Delta V_{GS1-2}}{\Delta T}$	Gate to Source Threshold Voltage Differential with Temperature ⁴			100	u\//°C	V _{DS} = -15V, I _D = -500µA T _S = -55 TO +25 °C
$\frac{\Delta V_{GS1-2}}{\Delta T}$	Gate to Source Threshold Voltage Differential with Temperature ⁴			100	μν/ Ο	V _{DS} = -15V, I _D = <mark>-500µA</mark> T _S = +25 TO +125 °C

ELECTRICAL CHARACTERISTICS @ 25 °C (unless otherwise stated) (V_{SB} = 0V unless otherwise stated)

SYMBOL	CHARACTERISTIC	MIN	TYP	MAX	UNITS	CONDITIONS	
BV _{DSS}	Drain to Source Breakdown Voltage	-40		<u> </u>	V	I _D = -10μΑ	
BV _{SDS}	Source to Drain Breakdown Voltage	-40				$I_{S} = -10 \mu A, V_{BD} = 0 V$	
V _{GS}	Gate to Source Voltage	-3.0		-6.5		V _{DS} = -15V, I _D = -500µA	
V	Gate to Source Threshold Voltage -2.0 -5.0 -2.0 -5.0		$V_{DS} = V_{GS}, I_D = -10 \mu A$				
V GS(th)		-2.0		-5.0		V _{DS} = -15V, I _D = -500µA	
IGSSR	Reverse Gate Leakage Current			10		V _{GS} = 40V	
I _{GSSF}	Forward Gate Leakage Current			-10	pА	V _{GS} = -40V	
I _{DSS}	Drain Leakage Current "Off"			-200		V _{DS} = -15V	
	Source to Drain Leakage Current "Off"			-400		V_{SD} = -15V, V_{DB} = 0V	
ID(on)	Drain Current "On"	-5.0		-30.0	mA	V_{DS} = -15V, V_{GS} = -10V	

SYMBOL					
g _{fs}	Forward Transconductance ⁵	1500	4000	119	V _{DS} = -15V, I _D = -5mA, <i>f</i> = 1kHz
Y _{os}	Output Admittance		300	μο	
r _{ds(on)}	Drain to Source "On" Resistance		300	Ω	V _{DS} = -20V, I _D = -100µA
C _{rss}	Reverse Transfer Capacitance		1.0		
C _{iss}	Input Capacitance Output Shorted		4.5	pF	V _{DS} = -15V, I _D = -5mA, <i>f</i> = 1MHz
Coss	Output Capacitance Input Shorted		3.0		

ELECTRICAL CHARACTERISTICS CONT. @ 25 °C (unless otherwise stated) (V_{SB} = 0V unless otherwise stated)

SWITCHING CHARACTERISTICS

SYMBOL	CHARACTERISTIC	MIN	TYP	MAX	UNITS	CONDITIONS
t _{d(on)}	Turn On Delay Time			15		
tr	Turn On Rise Time			30	ns	$V_{DD} = -15V, I_{D(on)} = -5mA,$ $R_{C} = R_{L} = 1.4kO$
t _{off}	Turn Off Time			50		



1. Absolute maximum ratings are limiting values above which serviceability may be impaired.

- 2. Per transistor.
- 3. Approximately doubles for every 10 $^{\circ}$ C increase in T_A.
- 4. Pulse: t = 300μ s, Duty Cycle $\leq 3\%$
- 5. Measured at end points, T_A and T_B .

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